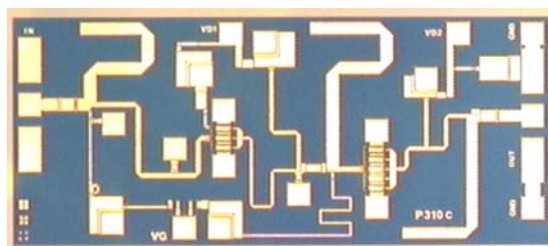


FEATURES

- 21.0 – 24.0 GHz Operating Frequency Range
- 24.0dBm Output Power at 1dB Compression
- 14.0 dB Typical Small Signal Gain
- -40dBc OIMD3 @Each Tone Pout 14dBm

APPLICATIONS

- Point-to-point and point-to-multipoint radio
- Military Radar Systems



Dimension: 2250um X 1000um
 Thickness: 75um ± 13um



Caution! ESD sensitive device.

ELECTRICAL CHARACTERISTICS ($T_a = 25\text{ }^\circ\text{C}$, 50 ohm, VDD=7V, IDQ=170mA)

SYMBOL	PARAMETER/TEST CONDITIONS	MIN	TYP	MAX	UNITS
F	Operating Frequency Range	21.0		24.0	GHz
P1dB	Output Power at 1dB Gain Compression	23.0	24.0		dBm
Gss	Small Signal Gain	11.0	14.0		dB
OIMD3	Output 3 rd Order Intermodulation Distortion @ $\Delta f=10\text{MHz}$, Each Tone Pout 14dBm		-40	-37	dBc
Input RL	Input Return Loss		-10	-8	dB
Output RL	Output Return Loss		-10	-8	dB
Idss	Saturate Drain Current $V_{DS}=3\text{V}$, $V_{GS}=0\text{V}$	211	264	317	mA
V_{DD}	Power Supply Voltage		7	8	V
Rth	Thermal Resistance (Au-Sn Eutectic Attach)		34		$^\circ\text{C/W}$
Tb	Operating Base Plate Temperature	-35		+85	$^\circ\text{C}$

ABSOLUTE MAXIMUM RATINGS FOR CONTINUOUS OPERATION^{1,2}

SYMBOL	CHARACTERISTIC	VALUE
V_{DS}	Drain to Source Voltage	8 V
V_{GS}	Gate to Source Voltage	-4 V
I_{DD}	Drain Current	Idss
I_{GSF}	Forward Gate Current	4mA
P_{IN}	Input Power	@ 3dB compression
T_{CH}	Channel Temperature	150 $^\circ\text{C}$
T_{STG}	Storage Temperature	-65/150 $^\circ\text{C}$
P_T	Total Power Dissipation	3.4W

1. Operating the device beyond any of the above rating may result in permanent damage.

2. Bias conditions must also satisfy the following equation $V_{DS} * I_{DS} < (T_{CH} - T_{HS}) / R_{TH}$; where T_{HS} = ambient temperature

Specifications are subject to change without notice.

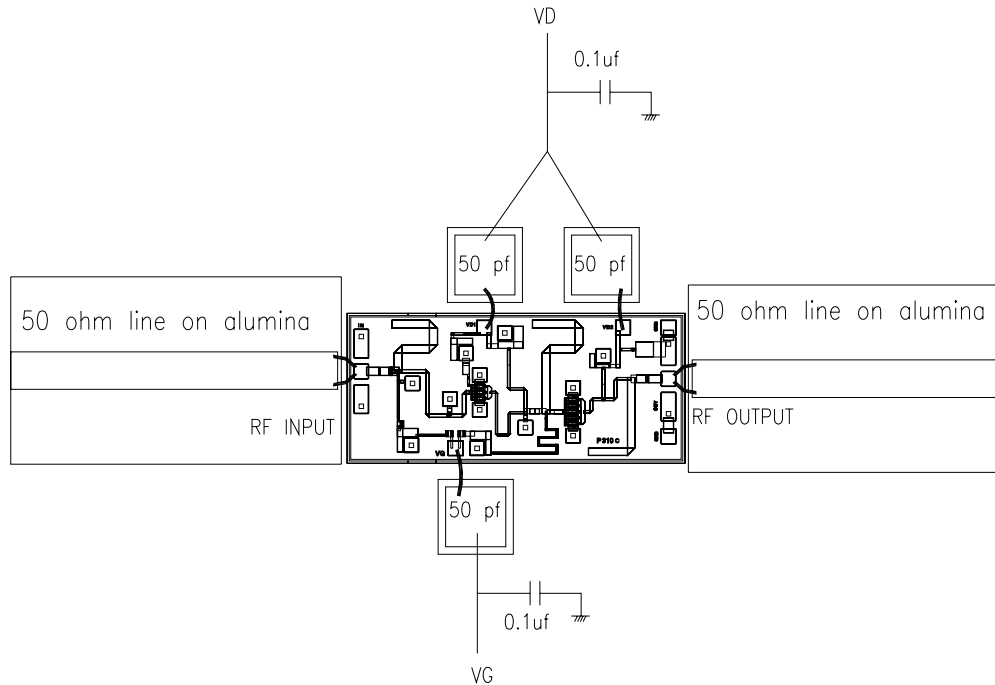
Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085

Phone: 408-737-1711 Fax: 408-737-1868 Web: www.excelics.com

page 1 of 3

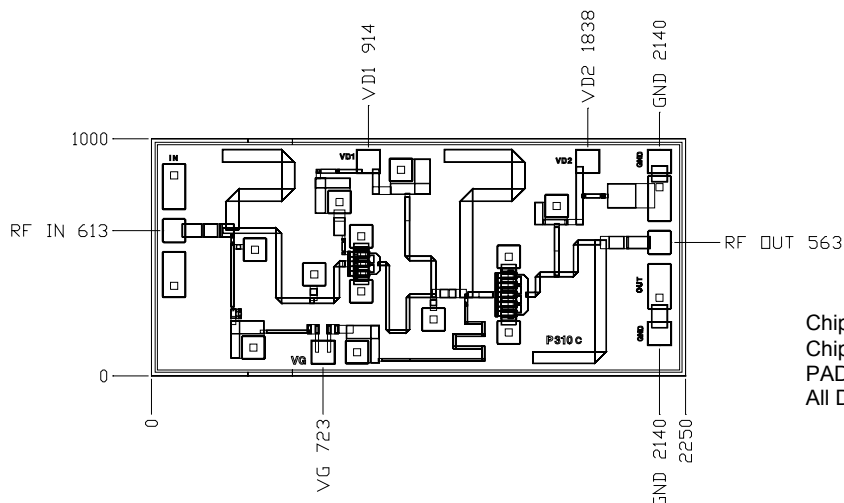
Revised May 2008

ASSEMBLY DRAWING



The length of RF wires should be as short as possible. Use at least two wires between RF pad and 50 ohm line and separate the wires to minimize the mutual inductance.

CHIP OUTLINE



Chip Size 1000 x 2250 microns
 Chip Thickness: 75 ± 13 microns
 PAD Dimensions: 100 x 100 microns
 All Dimensions in Microns

Specifications are subject to change without notice.



EMP310

UPDATED 05/08/2008

21.0 – 24.0 GHz Power Amplifier MMIC

DISCLAIMER

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AS HERE IN:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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page 3 of 3
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